Single Channel, DC Sensing Input, Phototransistor Optocoupler In Stretched Body SOP 4-Pin



Description

The FODM100x Series, single channel, DC sensing input, optocoupler consists of one gallium arsenide (GaAs) infrared light emitting diode optically coupled to one phototransistor, in a stretched body SOP 4–pin package. The input–output isolation voltage, V_{ISO} , is rated at 5,000 VAC_{RMS}.

Features

- ≥ 8 mm Creepage and Clearance Distance, and ≥ 0.4 mm Insulation Distance to Achieve Reliable and High Voltage Insulation
- Safety and Regulatory Approvals
- UL1577, 5,000 VAC_{RMS} for 1 min
- DIN EN/IEC60747-5-5, 890 V Peak Working Voltage
- High Breakdown Collector to Emitter Voltage, BV_{CEO} = 70 V Minimum
- Extended Industrial Temperate Range, -40 to 110°C
- Current Transfer Ratio at $I_F = 5 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$
- FODM1007: 80 to 160%
- FODM1008: 130 to 260%
- FODM1009: 200 to 400%
- These are Pb-Free Devices

Applications

- Primarily Suited for DC-DC Converters
- For Ground Loop Isolation, Signal to Noise Isolation
- Communications Adapters, Chargers
- Consumer Appliances, Set-Top Boxes
- Industrial Power Supplies, Motor Control, Programmable Logic Control

Related Resources

- https://www.onsemi.com/products/optoelectronics/
- www.onsemi.com/datsheets/HM/HMHA2801.pdf



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MARKING DIAGRAM



- 100x = Specific Device Code (x = 7, 8, 9) $V_{\text{DIN}} = \text{DIN} \text{EN}/\text{IEC60747} = 5 - 5 \text{Option}$ (on
 - = DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
- X = Last Digit Year Code
- YY = Two Digit Work Week

L

= Assembly Package Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

SAFETY AND INSULATION RATINGS (As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.)

Parameter		Characteristics
Installation Classifications per DIN VDE	<150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	<300 V _{RMS}	-
Climatic Classification	40/110/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10 \text{ s}$, Partial Discharge < 5 pC	1,426	V _{peak}
	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1 \text{ s}$, Partial Discharge < 5 pC	1,671	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	890	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6.000	V _{peak}
	External Creepage	≥8.0	mm
	External Clearance	≥8.0	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥0.4	mm
Τ _S	Case Temperature (Note 1)	150	°C
I _{S,INPUT}	Input Current (Note 1)	200	mA
S,OUTPUT	Output Power (Note 1)	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	>10 ⁹	Ω

1. Safety limit values - maximum values allowed in the event of a failure.

 PD_C

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$, unless otherwise noted)

Detector Power Dissipation @ T_A = 25°C (Note 2)

Derate Above 25°C

Symbol	Parameter	Value	Unit
TOTAL PA	CKAGE		-
T _{STG}	Storage Temperature	–55 to +150	°C
T _{OPR}	Operating Temperature	-40 to +110	°C
Τ _J	Junction Temperature	-40 to +125	°C
EMITTER			
I _{F(avg)}	Continuous Forward Current	50	mA
I _{F(pk)}	Continuous Forward Current (1 µs Pulse, 300 pps)	1	A
VR	Reverse Input Voltage	6	V
PD _{LED}	LED Power Dissipation @ $T_A = 25^{\circ}C$ (Note 2)	100	mW
	Derate Above 25°C	0.9	mW/°C
DETECTO	3		
Ι _C	Continuous Collector Current	50	mA
V _{CEO}	Collector-Emitter Voltage	70	V
V_{ECO}	Emitter-Collector Voltage	7	V
			1

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

150

1.47

mW

mW/°C

2. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$ unless otherwise specified.

INDIVIDUAL COMPONENT CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
EMITTER					-		
V _F	Forward Voltage	All	I _F = 50 mA	-	1.4	1.6	V
I _R	Reverse Current	All	V _R = 4 V	-	-	10	μA
DETECTOR							
BV _{CEO}	Breakdown Voltage Collector to Emitter	All	$I_{C} = 1 \text{ mA}, I_{F} = 0$	70	_	-	V
BV_{ECO}	Emitter to Collector	All	I _E = 0.1 mA, I _F = 0	7	-	-	V
I _{CEO}	Collector Dark Current	All	V _{CE} = 70 V, I _F = 0	-	-	100	nA
C _{CE}	Capacitance	All	V _{CE} = 0 V, f = 1 MHz	-	5	-	pF

DC TRANSFER CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
CTR	DC Current Transfer Ratio	FODM1007	I _F = 5 mA, V _{CE} = 5 V	80	-	160	%
		FODM1008		130	_	260	
		FODM1009		200	_	400	
V _{CE(SAT)}	Saturation Voltage	All	I _F = 10 mA, I _C = 1 mA	-	-	0.3	V

AC TRANSFER CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Мах	Unit
t _r	Rise Time (Non-Saturated)	All	I_{C} = 2 mA, V_{CE} = 5 V, R_{L} = 100 Ω	-	5.7	18.0	μs
t _f	Fall Time (Non-Saturated)	All	I_{C} = 2 mA, V_{CE} = 5 V, R_{L} = 100 Ω	-	8.5	18.0	

ISOLATION CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
V _{ISO}	Steady State Isolation Voltage	All	T_A = 25°C, R.H. < 50%, t =1.0 min., I_{I-O} \leq 20 μA	5,000	-	-	VAC _{RMS}

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS





Figure 1. Power Dissipation vs. Ambient Temperature



Figure 3. Non–Saturated Normalized Current Transfer Ratio vs. Ambient temperature

 $_{C}$ (NORMALIZED) = I_{C} (IF) / I_{C} (IF = 5 mA)

100

10

1

0.1

0.01

0.001

0.1

NORMALIZED TO:

25°C

I_F = 5 mA, V_{CE} = 5 V

Figure 2. Saturated Normalized Current Transfer Ratio vs. Ambient temperature



Figure 4. Forward Current vs. Forward Voltage



Figure 5. Normalized Current Collector vs. Forward Current

IF - FORWARD CURRENT (mA)

1

10



TYPICAL PERFORMANCE CHARACTERISTICS (continued)



Current

Current

REFLOW PROFILE





Table 1. REFLOW PROFILE

Profile Freature	Pb-Free Assembly Profile
Temperature Minimum (T _{smin})	150°C
Temperature Maximum (T _{smax})	200°C
Time (t _S) from (T _{smin} to T _{smax})	60 – 120 seconds
Ramp–up Rate (t _L to t _P)	3°C/second maximum
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second maximum
Time 25°C to Peak Temperature	8 minutes maximum

ORDERING INFORMATION

Part Number	Package	Shipping [†]
FODM1007	Stretched Body SOP 4-Pin	100 Units / Tube
FODM1007R2	Stretched Body SOP 4-Pin	3000 / Tape & Reel
FODM1007V	Stretched Body SOP 4–Pin, DIN EN/IEC60747–5–5 Option	100 Units / Tube
FODM1007R2V	Stretched Body SOP 4–Pin, DIN EN/IEC60747–5–5 Option	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NOTE: The product orderable part number system listed in this table also applies to the FODM1008, FODM1009 products.



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0.20 TYP



B. ALL DIMENSIONS ARE IN MILLIMETERS

C. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS

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